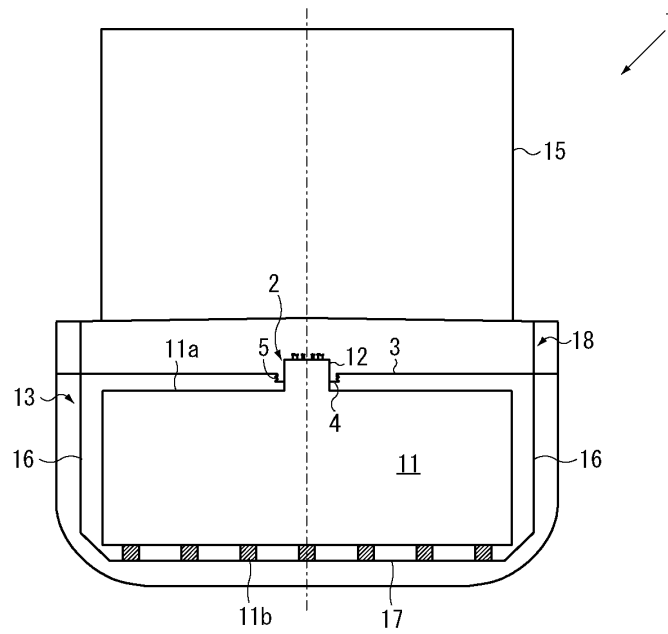


【図2】
(A)



(B)

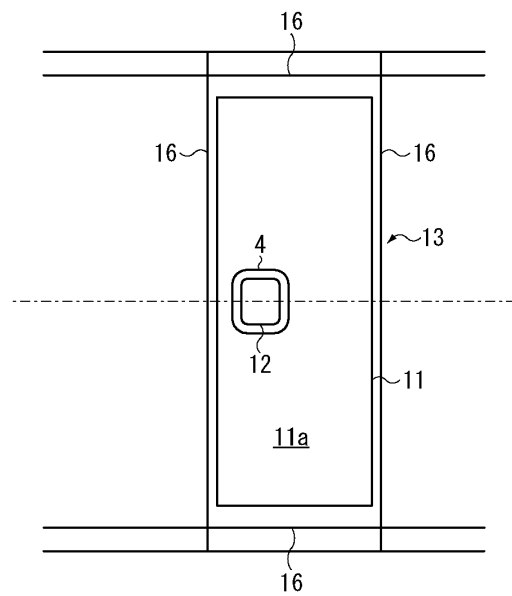
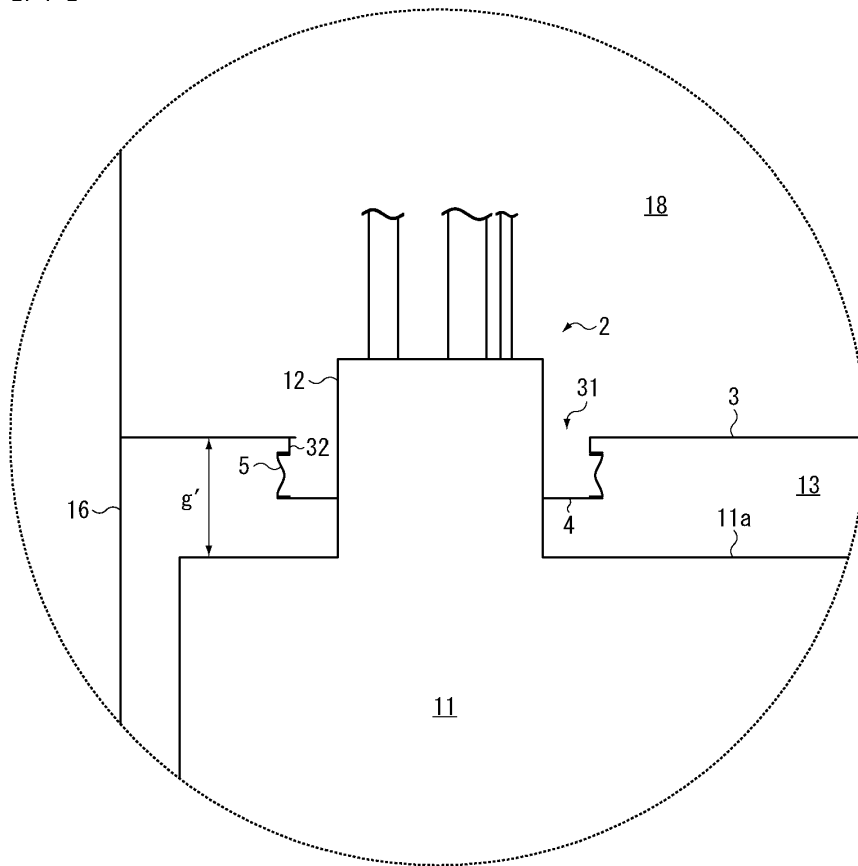
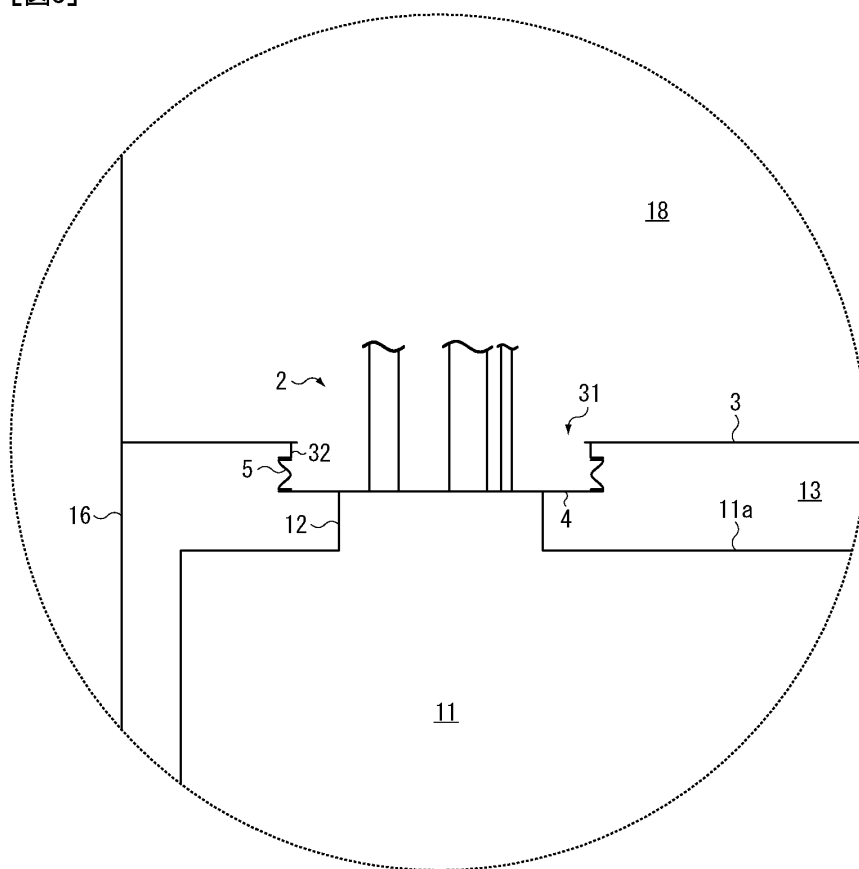


Fig. 1 is a cross-sectional view of a semiconductor device. The device includes a substrate 11, a trench 12, a gate 13, and a contact 14. The trench 12 has a depth h and a width g . The gate 13 is formed on the top surface of the substrate 11. The contact 14 is formed on the side surface of the trench 12. The device is surrounded by a protective layer 16.



[図5]



[図6]

